



DMTH6010SK3Q

#### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C	
60V	8mΩ @ V <sub>GS</sub> = 10V	70A	

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- DC-DC Converters
- Backlighting

#### Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Ensures On State Losses Are Minimized
- Excellent Q<sub>gd x</sub> R<sub>DS (ON)</sub> Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher
   Density End Products
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)

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Equivalent Circuit

• Weight: 0.33 grams (Approximate)



Top View

#### Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6010SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

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Pin Out Top View

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

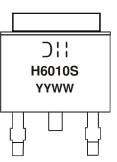
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



):' =Manufacturer's Marking
H6010S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

DMTH6010SK3Q Document number: DS38692 Rev. 2 - 2



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	16.3 13.6	А
Continuous Drain Current (Note 7)	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	ID	70 49	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	280	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	280	А
Avalanche Current, L=0.1mH		I <sub>AS</sub>	20	А
Avalanche Energy, L=0.1mH		E <sub>AS</sub>	27.7	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	PD	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	47	°C/W
Total Power Dissipation (Note 7)	PD	59	W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	2.5	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

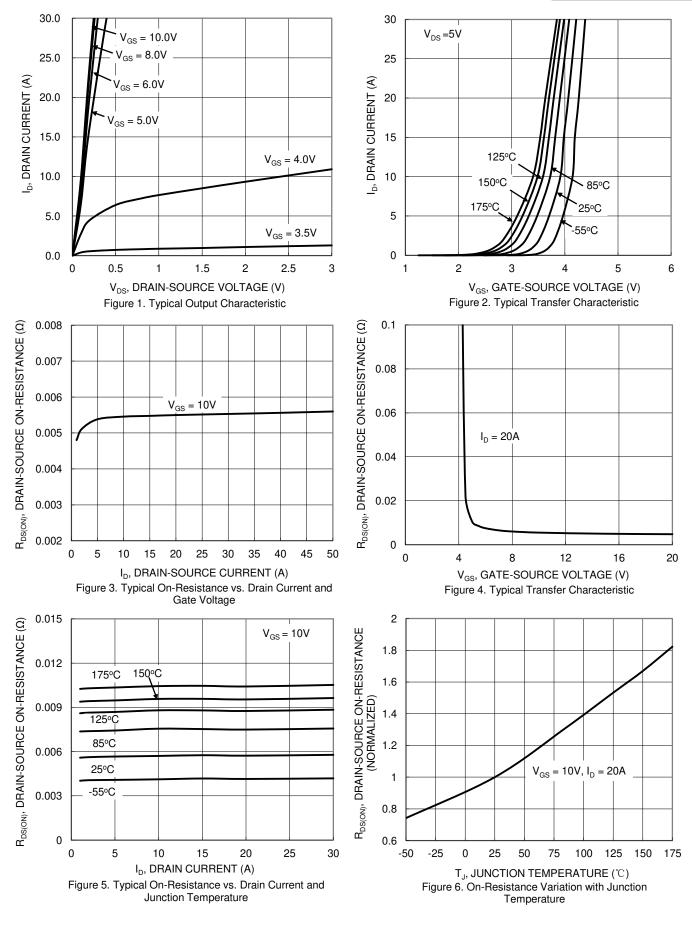
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	-	-	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	-	-	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	-	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	5.4	8	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.84	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	2841	-		$\label{eq:VDS} \begin{array}{l} V_{DS}=30V, \ V_{GS}=0V, \\ f=1MHz \end{array}$	
Output Capacitance	C <sub>oss</sub>	-	690	-	pF		
Reverse Transfer Capacitance	Crss	-	46	-			
Gate Resistance	Rg	-	0.55	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qq	-	38.1	-		V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A, V <sub>GS</sub> = 10V	
Gate-Source Charge	Q <sub>gs</sub>	-	8.3	-	nC		
Gate-Drain Charge	Q <sub>qd</sub>	-	9.3	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	8.6	-		$\label{eq:VDD} \begin{split} V_{DD} &= 30V, \ V_{GS} = 10V, \\ I_D &= 20A, \ R_G = 3\Omega \end{split}$	
Turn-On Rise Time	t <sub>R</sub>	-	8.2	-	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	17.4	-	ns		
Turn-Off Fall Time	tF	-	5.7	-	]		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	33.8	-	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	35.6	-	nC I <sub>F</sub> = 20A, di/dt = 100A/µs		

Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Device mounted on infinite heat sink and measured by thermal couple attached on bottom heat sink of package.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

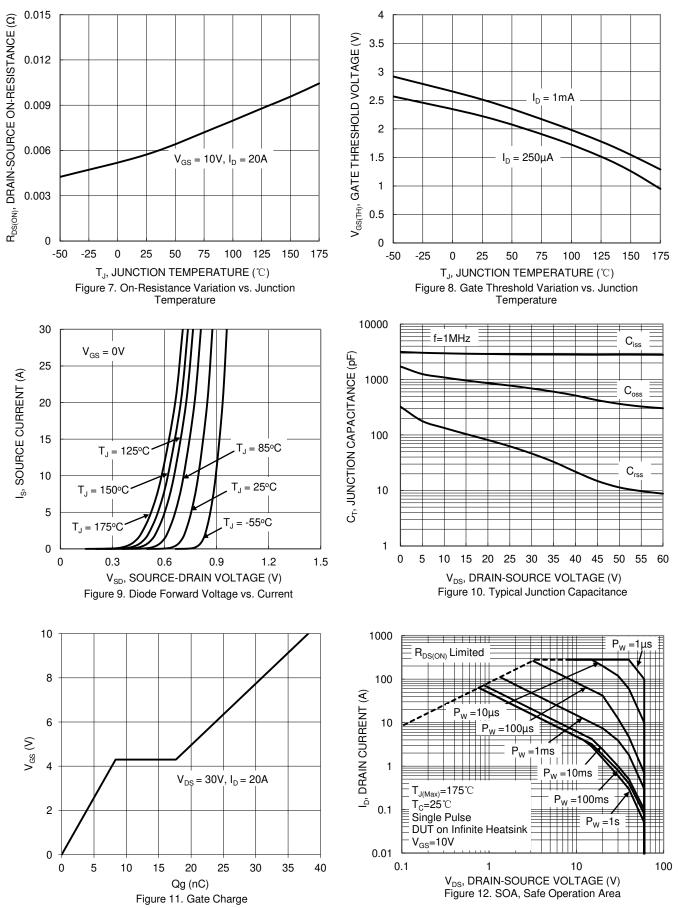


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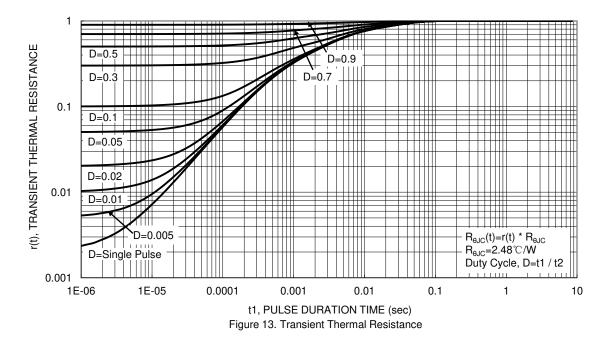


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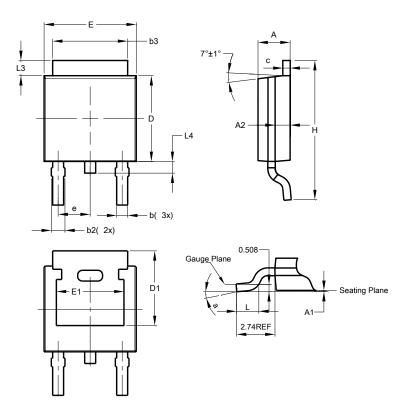






## Package Outline Dimensions

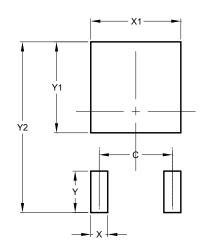
Please see http://www.diodes.com/package-outlines.html for the latest version.



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TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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